

	Type	Time Stamp	L #	Hits	Search Text	DBs
1	BRS	2003/01/03 10:35	L1	485	349/141	USPA T; US-P GPUB ; EPO; JPO; DERW ENT; IBM _TDB
2	BRS	2003/01/03 10:45	L2	227	1 and semiconductor	USPA T; US-P GPUB ; EPO; JPO; DERW ENT; IBM _TDB
3	BRS	2003/01/03 16:37	L3	13	2 and light adj (intercept\$3 or absorb\$3)	USPA T; US-P GPUB ; EPO; JPO; DERW ENT; IBM _TDB
4	BRS	2003/01/03 10:54	L4	16	1 and samsung	USPA T; US-P GPUB ; EPO; JPO; DERW ENT; IBM _TDB

	Type	Time Stamp	L #	Hits	Search Text	DBs
5	BRS	2003/01/03 10:54	L5	990	349/43	USPAT; US-P GPUB; EPO; JPO; DERWENT; IBM_TDB
6	BRS	2003/01/03 14:58	L6	42	5 and light adj (intercept\$3 or absorb\$3)	USPAT; US-P GPUB; EPO; JPO; DERWENT; IBM_TDB
7	BRS	2003/01/03 13:56	L7	320	5 and (light adj (intercept\$3 or absorb\$3) or black adj matrix)	USPAT; US-P GPUB; EPO; JPO; DERWENT; IBM_TDB
8	BRS	2003/01/03 14:05	L8	25	5 and (semiconductor with black adj matrix)	USPAT; US-P GPUB; EPO; JPO; DERWENT; IBM_TDB

	Type	Time Stamp	L #	Hits	Search Text	DBs
9	BRS	2003/01/03 14:08	L9	180	semiconductor with black adj matrix	USPAT; US-PGPUB; ;EPO; JPO; DERWENT; IBM-TDB
10	BRS	2003/01/03 14:06	L10	4	9 and light adj intercept\$3	USPAT; US-PGPUB; ;EPO; JPO; DERWENT; IBM-TDB
11	BRS	2003/01/03 14:19	L11	85	9 and common adj electrode	USPAT; US-PGPUB; ;EPO; JPO; DERWENT; IBM-TDB
12	BRS	2003/01/03 14:18	L12	4041	light adj intercept\$3	USPAT; US-PGPUB; ;EPO; JPO; DERWENT; IBM-TDB

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13	BRS	2003/01/03 14:19	L14	8	13 and common adj electrode	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM-TDB
14	BRS	2003/01/03 15:55	L13	119	semiconductor with light adj intercept\$3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM-TDB
15	BRS	2003/01/03 14:27	L15	20	13 and liquid adj crystal	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM-TDB
16	BRS	2003/01/03 14:30	L16	2	5247289.pn.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM-TDB
17	BRS	2003/01/03 14:30	L17	1	"4842371".PN.	USPAT
18	BRS	2003/01/03 14:31	L18	1	"4733948".PN.	USPAT
19	BRS	2003/01/03 14:31	L19	1	"4687298".PN.	USPAT
20	BRS	2003/01/03 14:35	L20	1	"4431271".PN.	USPAT

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21	BRS	2003/01/03 14:35	L21	1	"4393380".PN.	USPAT
22	BRS	2003/01/03 15:09	L22	9	5 and light adj intercept\$3	USPAT; US-P GPUB; EPO; JPO; DERW ENT; IBM TDB
23	BRS	2003/01/03 15:10	L23	2	1 and (light adj intercept\$3 with semiconductor)	USPAT; US-P GPUB; EPO; JPO; DERW ENT; IBM TDB
24	BRS	2003/01/03 15:10	L24	1	5 and (light adj intercept\$3 with semiconductor)	USPAT; US-P GPUB; EPO; JPO; DERW ENT; IBM TDB
25	BRS	2003/01/03 15:26	L25	0	semiconductor adj form\$2 adj light adj intercept\$3	USPAT; US-P GPUB; EPO; JPO; DERW ENT; IBM TDB

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26	BRS	2003/01/03 15:28	L26	0	semiconductor adj form\$3 adj light adj intercept\$3	USPA T; US-P GPUB ; EPO; JPO; DERW ENT; IBM _TDB
27	BRS	2003/01/03 15:29	L27	0	semiconductor adj form\$3 adj black	USPA T; US-P GPUB ; EPO; JPO; DERW ENT; IBM _TDB
28	BRS	2003/01/03 15:51	L28	2	semiconductor near light adj intercept\$3	USPA T; US-P GPUB ; EPO; JPO; DERW ENT; IBM _TDB
29	BRS	2003/01/03 15:52	L29	0	amorphous near light adj intercept\$3	USPA T; US-P GPUB ; EPO; JPO; DERW ENT; IBM _TDB

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30	BRS	2003/01/03 15:52	L30	0	light adj intercept\$3 adj amorphous	USPA T; US-P GPUB ; EPO; JPO; DERW ENT; IBM TDB
31	BRS	2003/01/03 16:36	L31	19	amorphous adj black	USPA T; US-P GPUB ; EPO; JPO; DERW ENT; IBM TDB
32	BRS	2003/01/03 15:55	L32	13	13 and amorphous	USPA T; US-P GPUB ; EPO; JPO; DERW ENT; IBM TDB
33	BRS	2003/01/03 16:37	L33	122	2 and black adj matrix	USPA T; US-P GPUB ; EPO; JPO; DERW ENT; IBM TDB

	Type	Time Stamp	L #	Hits	Search Text	DBs
34	BRS	2003/01/03 16:37	L34	100	33 and amorphous	USPAT; US-P GPUB; EPO; JPO; DERWENT; IBM_TDB
35	BRS	2003/01/03 16:50	L35	1	"6266117".PN.	USPAT
36	BRS	2003/01/03 16:50	L36	1	"5978057".PN.	USPAT
37	BRS	2003/01/03 16:50	L37	1	"5907379".PN.	USPAT
38	BRS	2003/01/03 16:50	L38	1	"5852485".PN.	USPAT
39	BRS	2003/01/03 16:51	L39	1	"5796449".PN.	USPAT
40	BRS	2003/01/03 16:51	L40	1	"5754266".PN.	USPAT
41	BRS	2003/01/03 16:52	L41	1	"5745207".PN.	USPAT
42	BRS	2003/01/03 16:52	L42	1	"5731856".PN.	USPAT
43	BRS	2003/01/03 16:54	L43	1	"5598285".PN.	USPAT
44	BRS	2003/01/03 16:54	L44	1	"5334860".PN.	USPAT
45	BRS	2003/01/03 16:54	L45	1	"5212574".PN.	USPAT
46	BRS	2003/01/03 16:54	L46	1	"5162931".PN.	USPAT
47	BRS	2003/01/03 16:55	L47	1	"5107355".PN.	USPAT
48	BRS	2003/01/03 16:55	L48	1	"4804953".PN.	USPAT

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1	BRS	L1	485	349/141	USPA T; US-P GPUB ; EPO; JPO; DERW ENT; IBM — TDB	2003/01/0 3 10:35
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3	BRS	L3	13	2 and light adj (intercept\$3 or absorb\$3)	USPA T; US-P GPUB ; EPO; JPO; DERW ENT; IBM — TDB	2003/01/0 3 10:54
4	BRS	L4	16	1 and samsung	USPA T; US-P GPUB ; EPO; JPO; DERW ENT; IBM — TDB	2003/01/0 3 10:54

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6	BRS	L6	42	5 and light adj (intercept\$3 or absorb\$3)	USPA T; US-P GPUB ; EPO; JPO; DERW ENT; IBM — TDB	2003/01/0 3 14:17
7	BRS	L7	320	5 and (light adj (intercept\$3 or absorb\$3) or black adj matrix)	USPA T; US-P GPUB ; EPO; JPO; DERW ENT; IBM — TDB	2003/01/0 3 13:56
8	BRS	L8	25	5 and (semiconductor with black adj matrix)	USPA T; US-P GPUB ; EPO; JPO; DERW ENT; IBM — TDB	2003/01/0 3 14:05

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10	BRS	L10	4	9 and light adj intercept\$3	USPA T; US-P GPUB ; EPO; JPO; DERW ENT; IBM TDB	2003/01/0 3 14:06
11	BRS	L11	85	9 and common adj electrode	USPA T; US-P GPUB ; EPO; JPO; DERW ENT; IBM TDB	2003/01/0 3 14:19
12	BRS	L12	4041	light adj intercept\$3	USPA T; US-P GPUB ; EPO; JPO; DERW ENT; IBM TDB	2003/01/0 3 14:18

	Type	L #	Hits	Search Text	DBs	Time Stamp
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14	BRS	L13	119	semiconductor with light adj intercept\$3	USPA T; US-P GPUB ; EPO; JPO; DERW ENT; IBM — TDB	2003/01/0 3 14:27
15	BRS	L15	20	13 and liquid adj crystal	USPA T; US-P GPUB ; EPO; JPO; DERW ENT; IBM — TDB	2003/01/0 3 14:27
16	BRS	L16	2	5247289.pn.	USPA T; US-P GPUB ; EPO; JPO; DERW ENT; IBM — TDB	2003/01/0 3 14:30
17	BRS	L17	1	"4842371".PN.	USPA T	2003/01/0 3 14:30
18	BRS	L18	1	"4733948".PN.	USPA T	2003/01/0 3 14:31
19	BRS	L19	1	"4687298".PN.	USPA T	2003/01/0 3 14:31
20	BRS	L20	1	"4431271".PN.	USPA T	2003/01/0 3 14:35

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21	BRS	L21	1	"4393380".PN.	USPAT	2003/01/03 14:35